

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) An optically pumped semiconductor laser device comprising:

a surface-emitting vertical emission region; and

~~at least one~~ monolithically integrated pump radiation ~~source~~ sources for optically pumping the vertical emission region,

wherein the ~~at least one~~ pump radiation ~~source~~ sources are ~~is~~ set up and arranged in such a manner that the pump radiation enters the vertical emission region in the form of partial bundles of rays of radiation with different radiation directions so that the pump radiation and the fundamental mode of the vertical emission region have an overlap which is suitable for the excitation of this fundamental mode; and

wherein each of said pump radiation sources has a resonator having at least one cavity end facet arrangement which consists of two straight cavity end facets which are arranged at right angles to one another.

Claims 2-6. (Canceled).

7. (Currently Amended) The semiconductor laser device as claimed in claim [[6]]1, wherein the two straight cavity end facets are arranged in such a manner that the pump radiation is totally reflected on them in the resonator.

Claims 8-17. (Canceled).

18. (New) An optically pumped semiconductor laser device comprising:
a surface-emitting vertical emission region; and
monolithically integrated pump radiation sources for optically pumping the vertical emission region,
wherein the pump radiation sources are set up and arranged in such a manner that the pump radiation enters the vertical emission region in the form of partial bundles of rays of radiation with different radiation directions so that the pump radiation and the fundamental mode of the vertical emission region have an overlap which is suitable for the excitation of this fundamental mode; and
wherein one or more of the pump radiation sources have a folded resonator with two cavity end facets and at least one inner cavity facet.

19. (New) The semiconductor laser device as claimed in claim 18, wherein the at least one inner cavity facet is arranged in such a manner that the pump radiation is totally reflected on it in the resonator.

20. (New) The semiconductor laser device as claimed in claim 18, wherein the cavity end facets are broken crystal facets and the inner cavity facets are etched facets.

21. (New) An optically pumped semiconductor laser device comprising:
a surface-emitting vertical emission region; and
at least one monolithically integrated pump radiation source for optically pumping the vertical emission region,
wherein the at least one pump radiation source is set up and arranged in such a manner that the pump radiation enters the vertical emission region in the form of partial bundles of rays of radiation with different radiation directions so that the pump radiation and the fundamental mode of the vertical emission region have an overlap which is suitable for the excitation of this fundamental mode; and
wherein the transition from the at least one pump radiation source to the vertical emission region is curved and is distinguished by a change in the index of refraction so that the pump radiation is focused in the vertical emission region.

22. (New) The semiconductor laser device as claimed in claim 21, wherein the radiation of the pump radiation source is conducted through the vertical emission region several times in different directions.